- Drafts
  - BRS:
  - BRS:
  - BRS:
  - BRS: knall
  - BRS: 19 21 23
  - BRS: 32with 33
- Pending
- Active
  - L1: (50) ((((dop$4 impuri$33 (ion near$3 implant$33) diffus$4)) near6 (fin
- Failed
- Saved
  - S1: (1) 09/948877
  - S2: (1736) "KONINKLIJKE PHILIPS".as.
  - S3: (0) 10/753914
  - S4: (1) 10/728910
  - S5: (290) (finfet fin adj2 (fet mosfet mos transistor))
  - S6: (1) 10/429697
  - S7: (4) ("6316305" "4996574").pn.
  - S8: (2) ("6316305" "4998574 6445017").pn.
  - S9: (6) ("6316305" "4996574" "6445017").pn.
  - S10: (1) 10/614052
  - S11: (0) "6812119".pn.
  - S12: (62503) (SRAM static adj3 memory static adj RAM)

((((dop$4 impuri$33 (ion near$3 implant$33) diffus$4)
) near6 (fin body)) and ((finfet fin adj2 (fet mosfet mos transistor))
)) and (fin near6 body)) and ((@ad @pd) <"20031208")

Feb, 2005

U	Inventor	Document ID	Issue P	Title	Current	Current X	Retrieva	S	C	P			Image Do	P
1	Yeo, Yee-C	US 20040099885	2004	CMOS SRAM cell configured using mu	257/20								US 20040	
2	Fried, Davi	US 20030102518	2003	2	Finfet SRAM cell using low mobility pla	257/40	257/350;							US 20030
3	Nowak; Ed	US 6794718 B2	2004	1	High mobility crystalline planes in dou	257/34	438/149;							US 67947
4	Fried; Davi	US 6684582 B2	2003	1	Fin memory cell and method of fabrica	257/30	257/310;							US 66645
5	Nowak; Ed	US 6610578 B2	2003	3	Method for forming asymmetric dual g	438/30	257/E21.4							US 66105
6	Yeo, Yee-C	US 20050035415	2005	1	Multiple-gate transistors formed on bu	257/40	438/283							US 20050
7	Yeo, Yee-C	US 20040266077	2004	1	Structure and method for forming the	438/15								US 20040
8	Lee, Jong-	US 20040256647	2004	3	Strained silicon finFET device	257/28								US 20040
9	Boyanov, B	US 20040253774	2004	1	Double-gate transistor with enhanced	438/17	438/268							US 20040
10	Pham, Dani	US 20040219722	2004	1	METHOD FOR FORMING A DOUBLE-	438/15	257/401;							US 20040